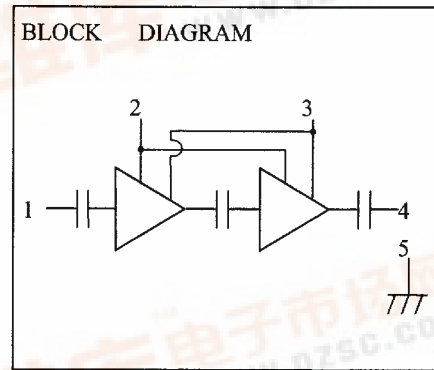
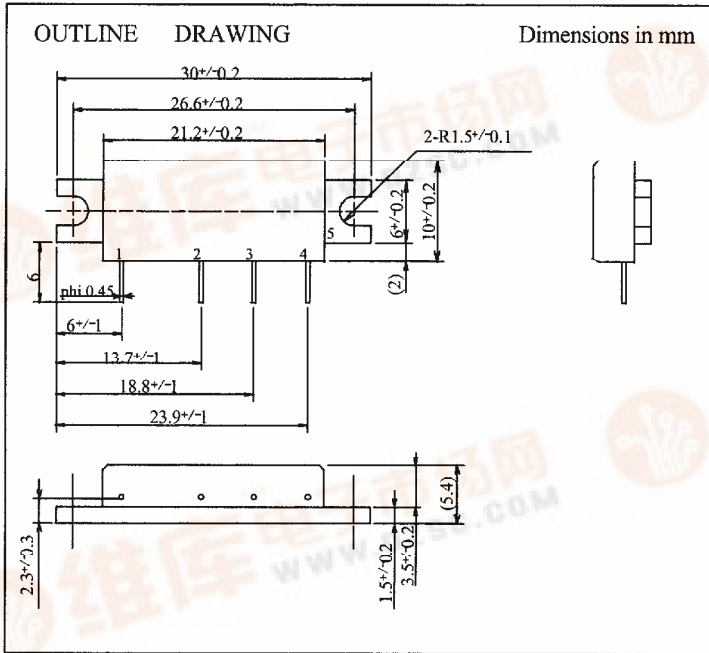


ATTENTION  
OBSERVE PRECAUTIONS  
FOR HANDLING  
ELECTROSTATIC  
SENSITIVE  
DEVICES

MITSUBISHI RF POWER MODULE

# M68776

Silicon MOS FET Power Amplifier, 135-175MHz 6.5W FM PORTABLE



PIN:  
1.Pin :RF INPUT  
2.VGG :GATE BIAS SUPPLY  
3.VDD :DRAIN BIAS SUPPLY  
4.Po :RF OUTPUT  
5.GND :FIN

MAXIMUM RATINGS (Tc=25deg.C UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	RATINGS	UNIT
VDD	SUPPLY VOLTAGE	VGG<3.5V,Zg=Zl=50ohms	9.2	V
VGG	GATE BIAS VOLTAGE		4	V
Pin	INPUT POWER	f=135-175MHz,Zg=Zl=50ohms	30	mW
Po	OUTPUT POWER	f=135-175MHz,Zg=Zl=50ohms	10	W
Tc(OP)	OPERATION CASE TEMPERATURE	f=135-175MHz,Zg=Zl=50ohms	-30 to +100	deg.C
Tstg	STORAGE TEMPERATURE		-40 to +110	deg.C

Note:Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25deg.C,Zg=Zl=50ohms UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	LIMITS		UNIT
			MIN	MAX	
f	FREQUENCY RANGE		135	175	MHz
Po	OUTPUT POWER	Vdd=7.2V,	6.5		W
Nt	TOTAL EFFICIENCY	Vgg=3.5V,	40		%
2fo	2nd HARMONIC	Pin=20mW		-25	dBc
VSWR in	INPUT VSWR			4	-
	Stability	Zg=50ohms, Vdd=4-9.2V, Load VSWR < 4:1	No parasitic oscillation		
	LOAD VSWR TOLERANCE	Vdd=9.2V,Pin=20mW,Po=6.5W (Vgg ADJUST), Zg=50ohms, Load VSWR =20:1	No degradation or destroy		-

ABOVE PARAMETERS, RATINGS, LIMITS AND CONDITIONS ARE SUBJECT TO CHANGE .

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

